

## Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	$I_D$
100V	6.7mΩ@10V	80A
	8.7mΩ@4.5V	



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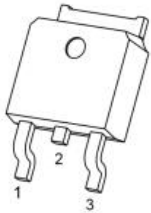
## Feature

- Fast Switching
- Low Gate Charge and R<sub>ds(on)</sub>
- 100% Single Pulse avalanche energy Test

## Applications

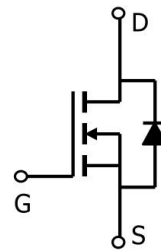
- Power switching application
- DC-DC Converter
- Power Management

## Package

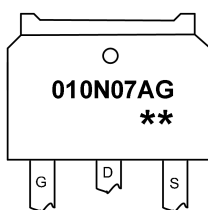


TO-252(G:1 D:2 S:3)

## Circuit diagram



## Marking



010N07AG : Product code  
 \*\* : Week code

## Order Information

Device	Package	Unite/Tape
SP010N07AGTH	TO-252	2500

### Absolute maximum ratings (Ta=25°C, unless otherwise noted)

Parameter	Symbol	Rating	Unit
Drain source voltage	V <sub>DS</sub>	100	V
Gate source voltage	V <sub>GS</sub>	±20	V
Continuous drain current(Tc=25°C)	I <sub>D</sub>	80	A
Pulsed drain current	I <sub>DM</sub>	320	A
Power dissipation(Tc=25°C)	P <sub>D</sub>	100	W
Single pulsed avalanche energy <sup>1)</sup>	E <sub>AS</sub>	358	mJ
Thermal resistance, junction-case	R <sub>θJC</sub>	1.25	°C/W
Operation and storage temperature	T <sub>stg</sub> , T <sub>j</sub>	-55 to 150	°C

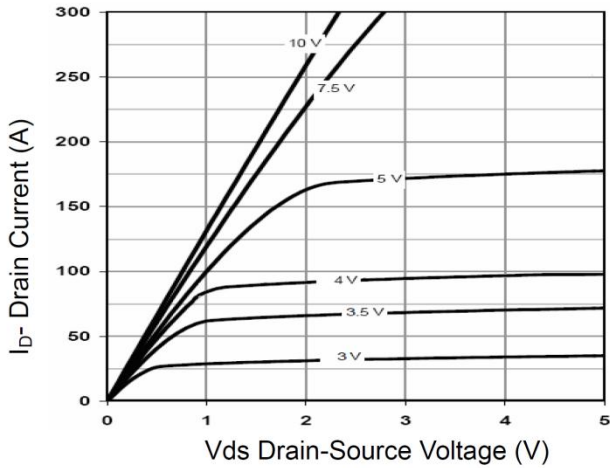
### Electrical characteristics (Ta=25°C, unless otherwise noted)

Characteristics	Symbol	Test Condition	Min	Typ	Max	Unit
<b>Static Characteristics</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	I <sub>D</sub> = 250μA, V <sub>GS</sub> = 0V	100	-	-	V
Drain Cut-Off Current	I <sub>DSS</sub>	V <sub>DS</sub> = 80V, V <sub>GS</sub> = 0V	-	-	1	μA
Gate Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V	-	-	±0.1	
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA	1.0	1.7	2.5	V
Drain-Source ON Resistance	R <sub>Ds(ON)</sub>	V <sub>GS</sub> = 10V, I <sub>D</sub> = 30A	-	6.7	8.5	mΩ
		V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 25A	-	8.7	12	
<b>Dynamic Characteristics</b>						
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> = 50V, V <sub>GS</sub> = 0V, f = 1.0MHz	-	1942	-	pF
Output Capacitance	C <sub>oss</sub>		-	388	-	
Reverse Transfer Capacitance	C <sub>rss</sub>		-	12	-	
<b>Switching Characteristics</b>						
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> =50V, V <sub>GS</sub> =10V, I <sub>D</sub> =30A	-	67	-	nC
Gate-Source Charge	Q <sub>gs</sub>		-	12	-	
Gate-Drain Charge	Q <sub>gd</sub>		-	21	-	
Turn-On Delay Time	t <sub>d(on)</sub>	V <sub>GS</sub> = 10V, V <sub>DS</sub> = 50V, RL=2.5Ω, R <sub>G</sub> = 6.0Ω	-	12	-	ns
Rise Time	t <sub>r</sub>		-	11	-	
Turn-Off Delay Time	t <sub>d(off)</sub>		-	42	-	
Fall Time	t <sub>f</sub>		-	6	-	
<b>Drain-Source Body Diode Characteristics</b>						
Source-Drain Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> = 1A, V <sub>GS</sub> = 0V	-	-	1.2	V

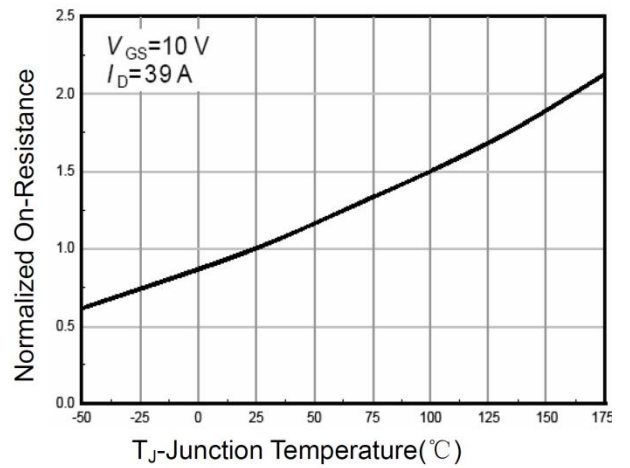
Note:

- E<sub>AS</sub> is tested at starting T<sub>j</sub> = 25°C, V<sub>DD</sub>=50V, V<sub>GS</sub> = 10V, L = 0.5mH, R<sub>G</sub>=25mΩ;

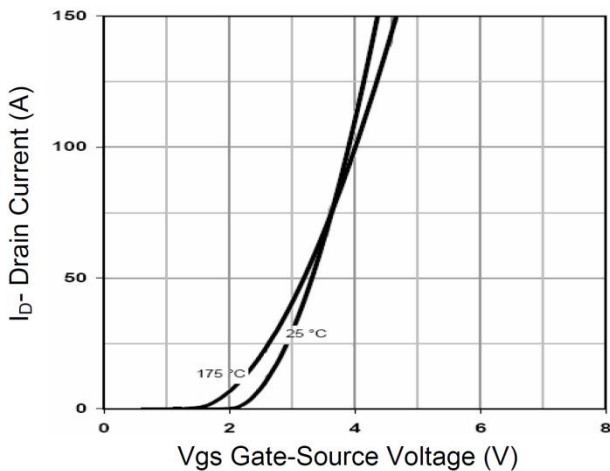
**Typical Characteristics**



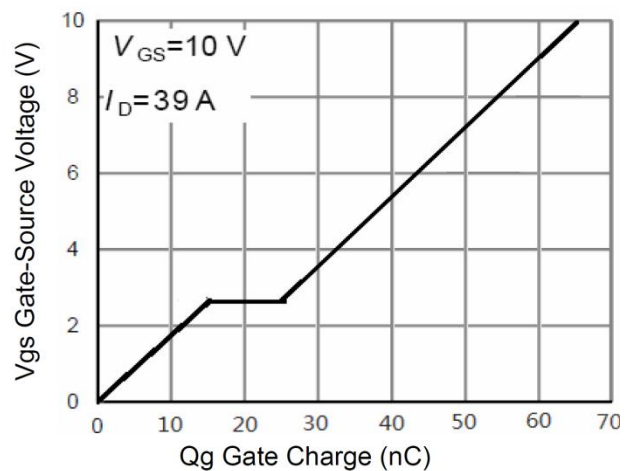
**Output Characteristics**



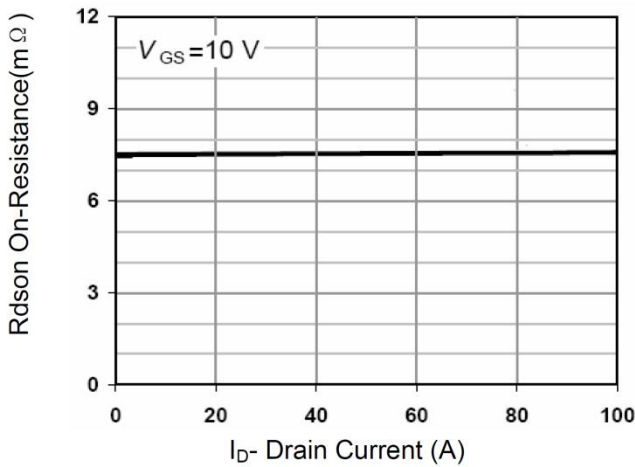
**Rdson-Junction Temperature**



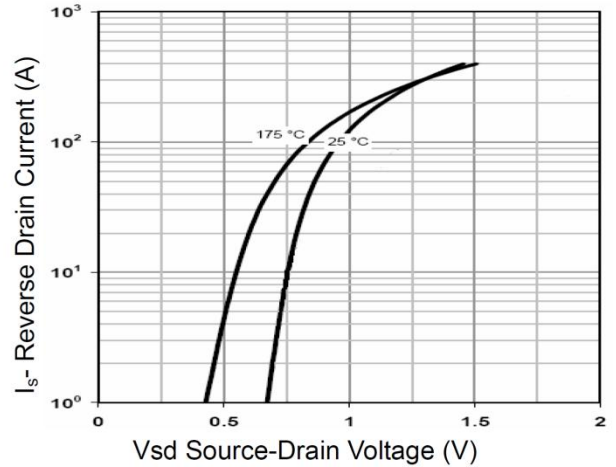
**Transfer Characteristics**



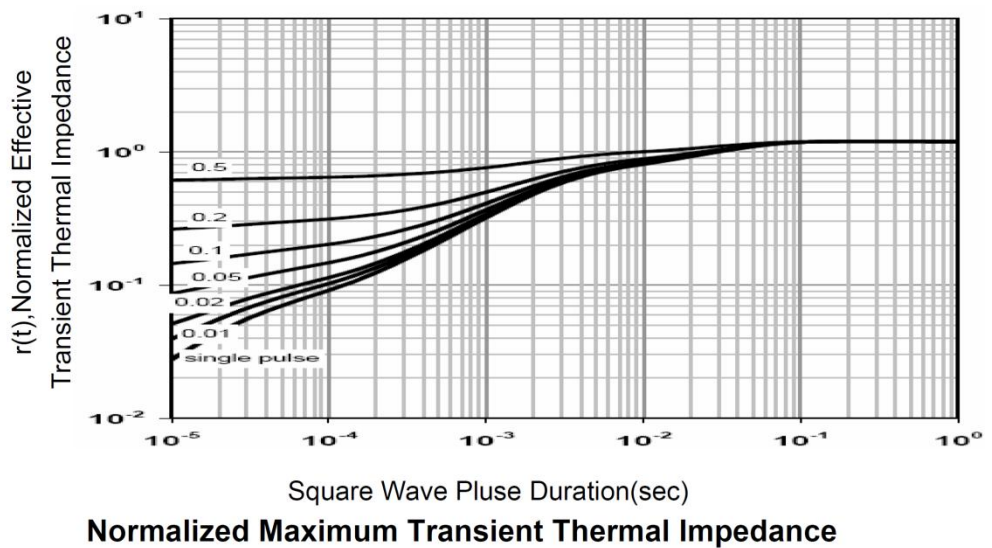
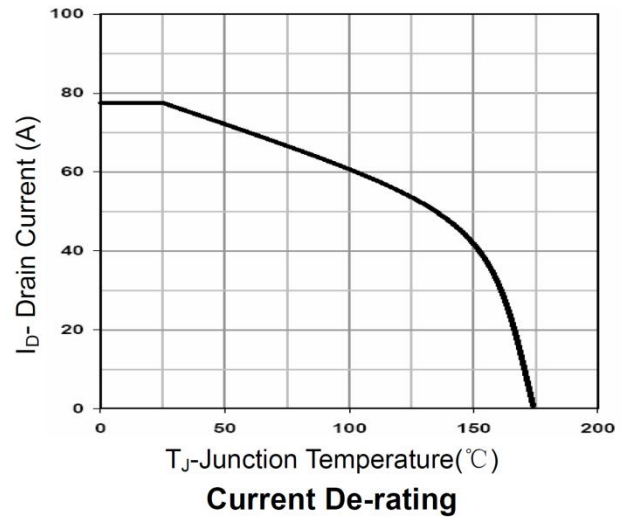
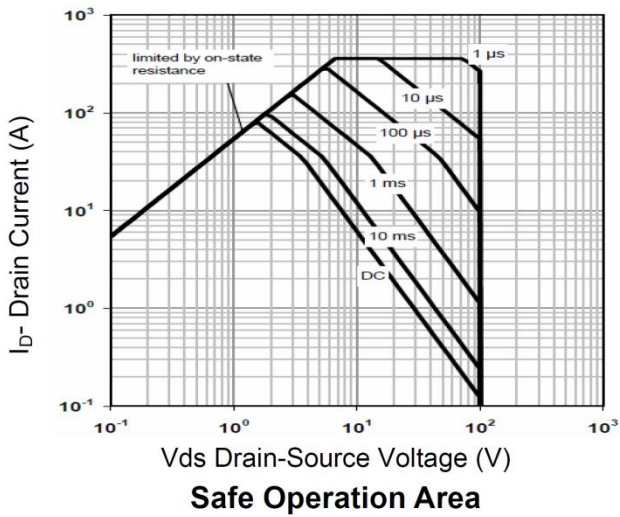
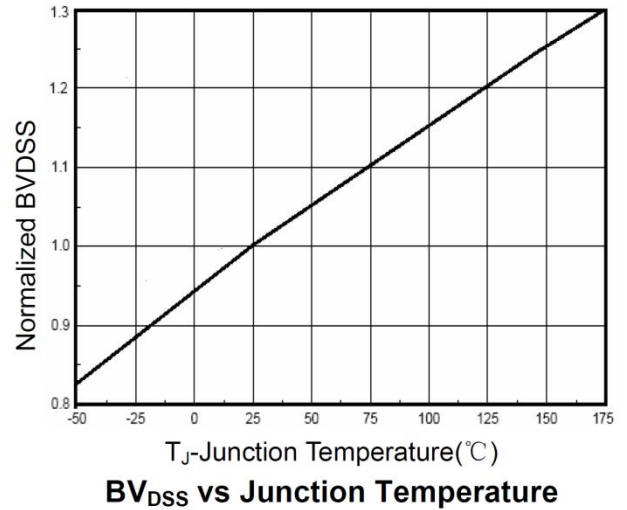
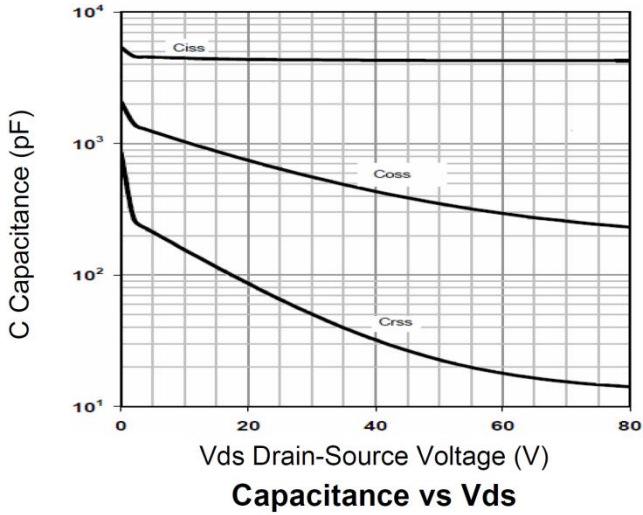
**Gate Charge**

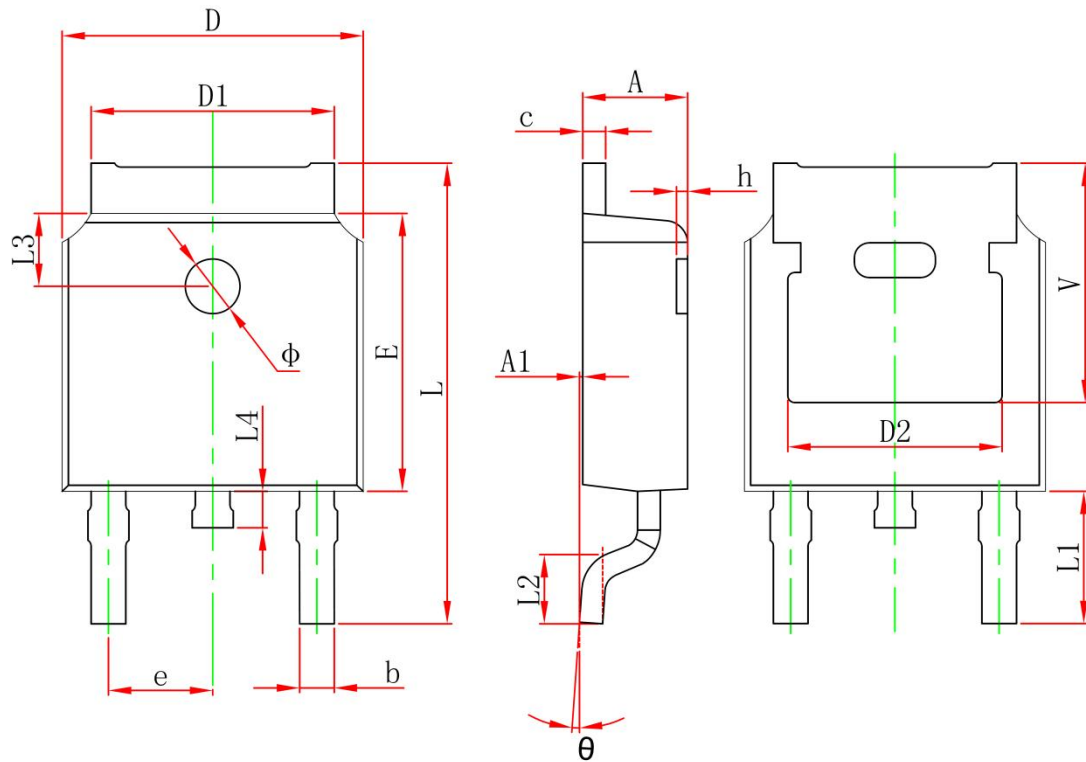


**Rdson- Drain Current**



**Source- Drain Diode Forward**



**TO-252 Package Information**


Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
b	0.660	0.860	0.026	0.034
c	0.460	0.580	0.018	0.023
D	6.500	6.700	0.256	0.264
D1	5.100	5.460	0.201	0.215
D2	4.830 REF.		0.190 REF.	
E	6.000	6.200	0.236	0.244
e	2.186	2.386	0.086	0.094
L	9.800	10.400	0.386	0.409
L1	2.900 REF.		0.114 REF.	
L2	1.400	1.700	0.055	0.067
L3	1.600 REF.		0.063 REF.	
L4	0.600	1.000	0.024	0.039
φ	1.100	1.300	0.043	0.051
θ	0°	8°	0°	8°
h	0.000	0.300	0.000	0.012
V	5.350 REF.		0.211 REF.	

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